





N-CHANNEL ENHANCEMENT MODE MOSFET

Features

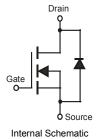
- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Totally Lead-Free & Fully RoHS compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

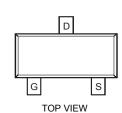
Mechanical Data

- Case: SOT-23
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020D
- Terminals: Finish Matte Tin annealed over Copper leadframe. Solderable per MIL-STD-202, Method 208
- Terminals Connections: See Diagram Below
- Weight: 0.008 grams (approximate)









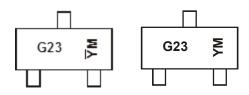
Ordering Information (Note 4)

Part Number	Case	Packaging	
DMG2302U-7	SOT-23	3000/Tape & Reel	

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html

Marking Information



G23 = Product Type Marking Code YM = Date Code Marking for SAT (Shanghai Assembly/ Test site) \(\bar{Y}\)M = Date Code Marking for CAT (Chengdu Assembly/ Test site) Y or \overline{Y} = Year (ex: A = 2013) M = Month (ex: 9 = September)

Date Code Key

Year	200	9	2010		2011	20	12	2013		2014	2	2015
Code	W		Х		Υ		7	Α		В		С
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



Maximum Ratings @TA = +25°C unless otherwise specified

Characte	ristic		Symbol	Value	Units
Drain-Source Voltage		V_{DSS}	20	V	
Gate-Source Voltage		V _{GSS}	±8	V	
Continuous Drain Current (Note 5) Steady $T_A = +25^{\circ}C$ State $T_A = +70^{\circ}C$			I _D	4.2 3.4	Α
Pulsed Drain Current (Note 6)			I _{DM}	27	Α

Thermal Characteristics

Characteristic	Symbol	Value	Unit	
Power Dissipation (Note 5)	T _A = +25°C T _A = +70°C	P	0.8 0.5	W
Thermal Resistance, Junction to Ambient @T _A = +25°	$R_{\theta JA}$	156	°C/W	
Operating and Storage Temperature Range	$T_{J_i} T_{STG}$	-55 to +150	°C	

Notes:

- 5. Device mounted on FR-4 PCB, with minimum recommended pad layout.
- 6. Repetitive rating, pulse width limited by junction temperature.

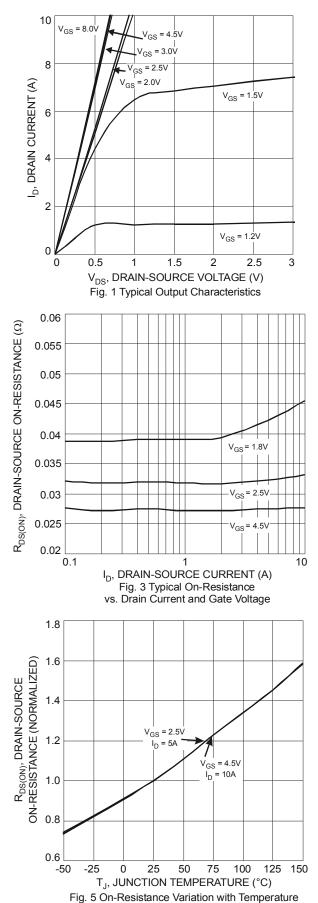
Electrical Characteristics @T_A = +25°C unless otherwise specified

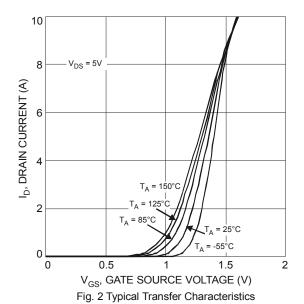
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition			
OFF CHARACTERISTICS (Note 7)									
Drain-Source Breakdown Voltage	BV _{DSS}	20	_	_	V	$V_{GS} = 0V, I_D = 10\mu A$			
Zero Gate Voltage Drain Current T _J = +25°C	I _{DSS}	_	_	1.0	μΑ	$V_{DS} = 20V, V_{GS} = 0V$			
Gate-Source Leakage	I _{GSS}	-	_	±100	nA	$V_{GS} = \pm 8V$, $V_{DS} = 0V$			
ON CHARACTERISTICS (Note 7)	ON CHARACTERISTICS (Note 7)								
Gate Threshold Voltage	V _{GS(th)}	0.4	-	1.0	V	$V_{DS} = V_{GS}$, $I_D = 50\mu A$			
Static Drain-Source On-Resistance	D- 0 (0) 11			90 120	mΩ	$V_{GS} = 4.5V, I_D = 3.6A$			
Static Drain-Source On-Resistance	R _{DS (ON)}	_				$V_{GS} = 2.5V, I_D = 3.1A$			
Forward Transfer Admittance	Y _{fs}	_	13	_	S	$V_{DS} = 5V, I_{D} = 3.6A$			
Diode Forward Voltage	V_{SD}	-	0.75	1.0	V	$V_{GS} = 0V, I_{S} = 1A$			
DYNAMIC CHARACTERISTICS (Note 8)									
Input Capacitance	C _{iss}	_	594.3	_	pF	101/1/			
Output Capacitance	Coss	1	64.5	_	pF	V _{DS} = 10V, V _{GS} = 0V, f = 1.0MHz			
Reverse Transfer Capacitance	C _{rss}	_	57.7	_	pF	1 - 1.0WHZ			
Gate Resistance	R_{g}	-	1.5	_	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$			
Total Gate Charge	Qg	_	7.0	_	nC	45)/)/ 40)/			
Gate-Source Charge	Qgs	-	0.9	_	nC	$V_{GS} = 4.5V, V_{DS} = 10V,$ $I_{D} = 3.6A$			
Gate-Drain Charge	Q_{gd}	-	1.4	_	nC				
Turn-On Delay Time	t _{D(on)}	-	7.4	_	ns				
Turn-On Rise Time	t _r	-	9.8	_	ns	V _{DD} = 10V, V _{GS} = 4.5V,			
Turn-Off Delay Time	t _{D(off)}	_	28.1	_	ns	$R_L = 2.78\Omega, R_G = 1.0\Omega$			
Turn-Off Fall Time	t _f	_	6.7	_	ns				

Notes:

- 7. Short duration pulse test used to minimize self-heating effect. 8. Guaranteed by design. Not subject to production testing.







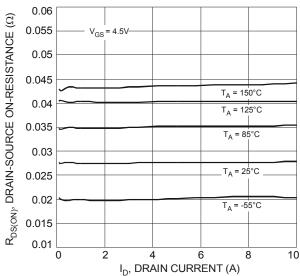
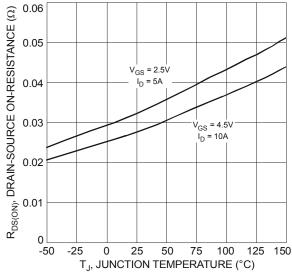


Fig. 4 Typical Drain-Source On-Resistance vs. Drain Current and Temperature





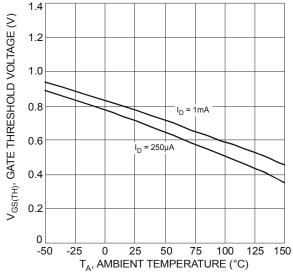
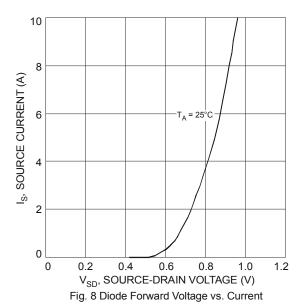
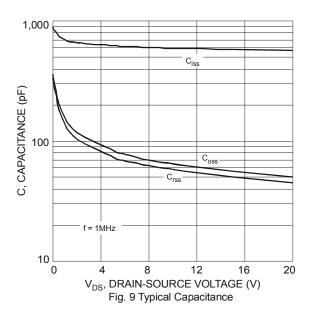
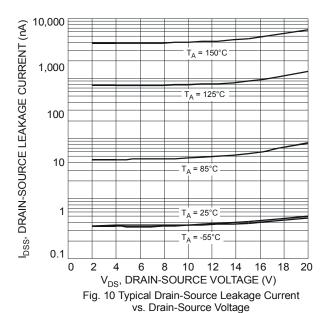


Fig. 7 Gate Threshold Variation vs. Ambient Temperature







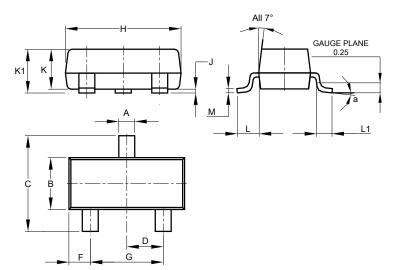
r(t), TRANSIENT THERMAL RESISTANCE D = 0.5 D = 0.30.1 D = 0.1 D = 0.05 $R_{\theta JA}(t) = r(t) * R_{\theta JA}$ $R_{\theta JA} = 157^{\circ}C/W$ D = 0.005 $\mathsf{T}_\mathsf{J} - \mathsf{T}_\mathsf{A} = \mathsf{P} * \mathsf{R}_{\theta \mathsf{J} \mathsf{A}}(\mathsf{t})$ Duty Cycle, D = t_1/t_2 0.001 0.00001 0.0001 0.001 0.01 0.1 1,000

 t_1 , PULSE DURATION TIME (s) Fig. 11 Transient Thermal Response



Package Outline Dimensions

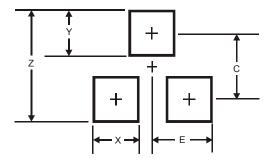
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.



SOT23							
Dim	Min	Max	Тур				
Α	0.37	0.51	0.40				
В	1.20	1.40	1.30				
C	2.30	2.50	2.40				
D	0.89	1.03	0.915				
F	0.45	0.60	0.535				
G	1.78 2.05		1.83				
Η	2.80	3.00	2.90				
7	0.013	0.10	0.05				
K	0.890	1.00	0.975				
K1	0.903	1.10	1.025				
L	0.45	0.61	0.55				
L1	0.25	0.55	0.40				
М	0.085	0.150	0.110				
α	8°						
All Dimensions in mm							

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
Z	2.9
Х	0.8
Υ	0.9
С	2.0
E	1.35



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